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Serial No. N/A

INFORMATION DISCLOSURE STATEMENT

Applicants: Shunpei YAMAZAKI et al.

Filing Date: July 31, 2001

Group Art Unit

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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
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Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
Examiner	/Thien Tran/		Date Considered			01/20/2011

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